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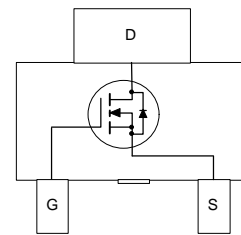
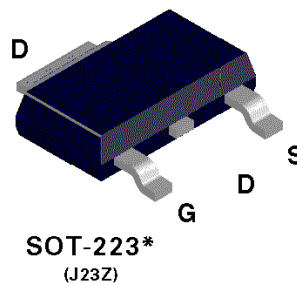
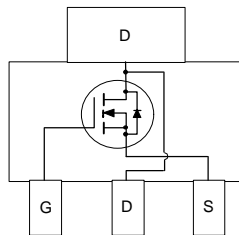
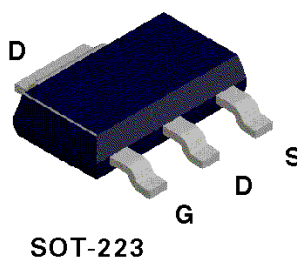
NDT014L N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 2.8 A, 60 V. $R_{DS(ON)} = 0.2 \Omega @ V_{GS} = 4.5 \text{ V}$
 $R_{DS(ON)} = 0.16 \Omega @ V_{GS} = 10 \text{ V}$.
- High density cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | NDT014L | Units |
|----------------|---|------------|------------------|
| V_{DSS} | Drain-Source Voltage | 60 | V |
| V_{GSS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current - Continuous (Note 1a) | ± 2.8 | A |
| | - Pulsed | ± 10 | |
| P_D | Maximum Power Dissipation (Note 1a) | 3 | W |
| | (Note 1b) | 1.3 | |
| | (Note 1c) | 1.1 | |
| T_J, T_{STG} | Operating and Storage Temperature Range | -65 to 150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| | | | |
|-----------------|---|----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 42 | $^\circ\text{C/W}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case (Note 1) | 12 | $^\circ\text{C/W}$ |

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units | |
|---|-----------------------------------|--|--|------|------|---------------|------|
| OFF CHARACTERISTICS | | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 60 | | | V | |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ | | | 25 | μA | |
| | | | $T_J = 55^\circ\text{C}$ | | 250 | μA | |
| I_{GSSF} | Gate - Body Leakage, Forward | $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | | | 100 | nA | |
| I_{GSSR} | Gate - Body Leakage, Reverse | $V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$ | | | -100 | nA | |
| ON CHARACTERISTICS (Note 2) | | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$ | 1 | 1.5 | 3 | V | |
| | | | $T_J = 125^\circ\text{C}$ | 0.8 | 1.1 | | 2 |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 4.5\text{ V}, I_D = 2.8\text{ A}$ | | 0.17 | 0.2 | Ω | |
| | | | $T_J = 125^\circ\text{C}$ | | 0.22 | | 0.36 |
| | | | $V_{GS} = 10\text{ V}, I_D = 3.4\text{ A}$ | | 0.12 | | 0.16 |
| $I_{D(on)}$ | On-State Drain Current | $V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$ | 5 | | | A | |
| | | | $V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$ | 10 | | | |
| G_{FS} | Forward Transconductance | $V_{GS} = 5\text{ V}, I_D = 2.8\text{ A}$ | | 4.2 | | S | |
| DYNAMIC CHARACTERISTICS | | | | | | | |
| C_{iss} | Input Capacitance | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$ | | 214 | | pF | |
| C_{oss} | Output Capacitance | | | 70 | | pF | |
| C_{rss} | Reverse Transfer Capacitance | | | 27 | | pF | |
| SWITCHING CHARACTERISTICS (Note 2) | | | | | | | |
| $t_{D(on)}$ | Turn - On Delay Time | $V_{DD} = 30\text{ V}, I_D = 3\text{ A},$ $V_{GEN} = 10\text{ V}, R_{GEN} = 12\ \Omega$ | | 6 | 12 | ns | |
| t_r | Turn - On Rise Time | | | 14 | 25 | ns | |
| $t_{D(off)}$ | Turn - Off Delay Time | | | 15 | 28 | ns | |
| t_f | Turn - Off Fall Time | | | 10 | 18 | ns | |
| Q_g | Total Gate Charge | | $V_{DS} = 10\text{ V},$ $I_D = 2.8\text{ A}, V_{GS} = 4.5\text{ V}$ | | 3.6 | 5 | nC |
| Q_{gs} | Gate-Source Charge | | | 0.8 | | nC | |
| Q_{gd} | Gate-Drain Charge | | | 1.4 | | nC | |

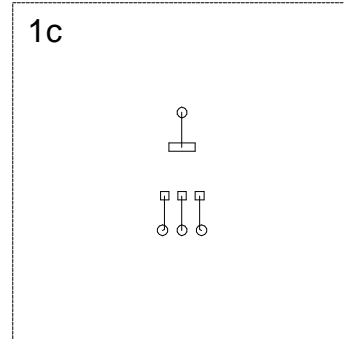
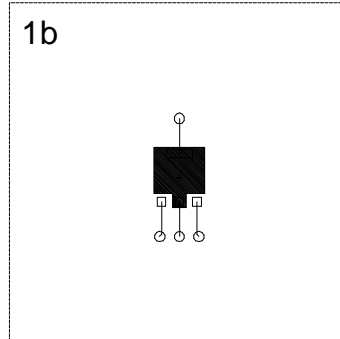
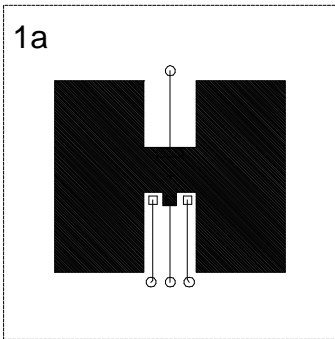
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|---|---|---|-----|------|-----|-------|
| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS | | | | | | |
| I_S | Maximum Continuous Drain-Source Diode Forward Current | | | | 2.3 | A |
| V_{SD} | Drain-Source Diode Forward Voltage | $V_{GS} = 0\text{ V}$, $I_S = 2.3\text{ A}$ (Note 2) | | 0.85 | 1.3 | V |
| t_{tr} | Reverse Recovery Time | $V_{GS} = 0\text{ V}$, $I_F = 2.3\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$ | | | 140 | ns |

Notes:

1. $P_D(t) = \frac{T_J - T_A}{R_{\theta JA}(t)} = \frac{T_J - T_A}{R_{\theta JC} + R_{\theta CA}(t)} = I_D^2(t) \times R_{DS(ON)@T_J}$ $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is defined by users. For general reference: Applications on 4.5"x5" FR-4 PCB under still air environment, typical $R_{\theta JA}$ is found to be:

- 42°C/W with 1 in² of 2 oz copper mounting pad.
- 95°C/W with 0.066 in² of 2 oz copper mounting pad.
- 110°C/W with 0.0123 in² of 2 oz copper mounting pad.



Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Typical Electrical Characteristics

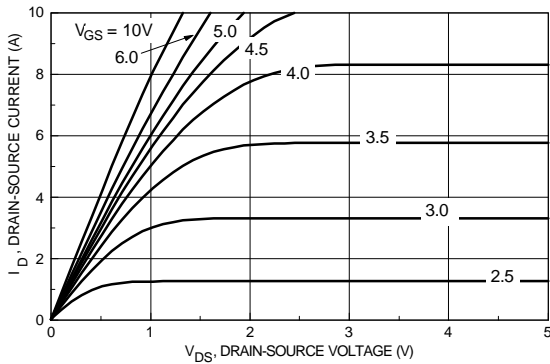


Figure 1. On-Region Characteristics.

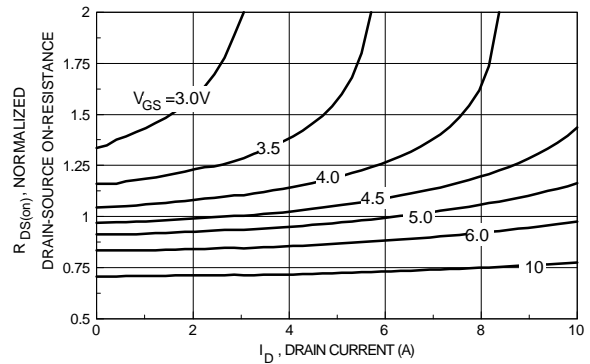


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

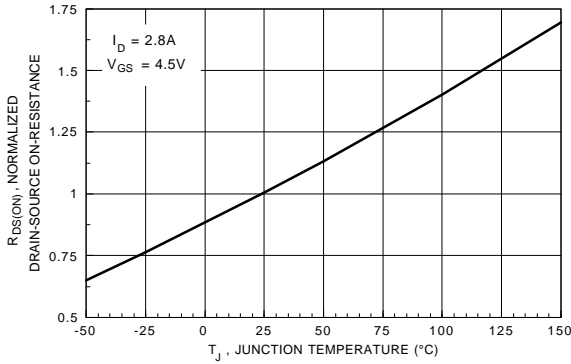


Figure 3. On-Resistance Variation with Temperature.

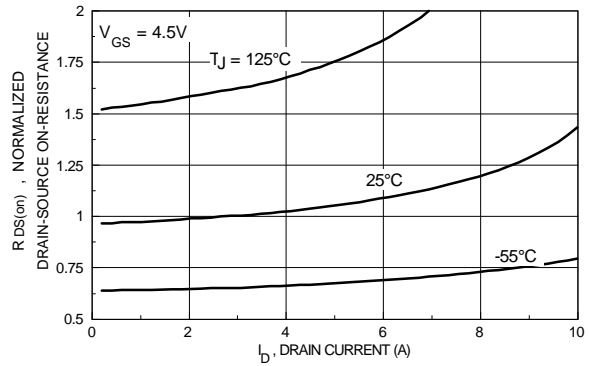


Figure 4. On-Resistance Variation with Drain Current and Temperature.

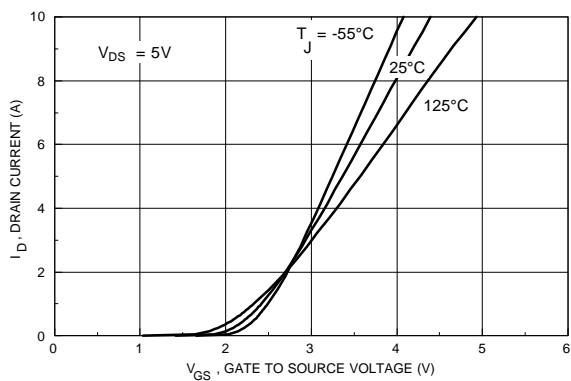


Figure 5. Transfer Characteristics.

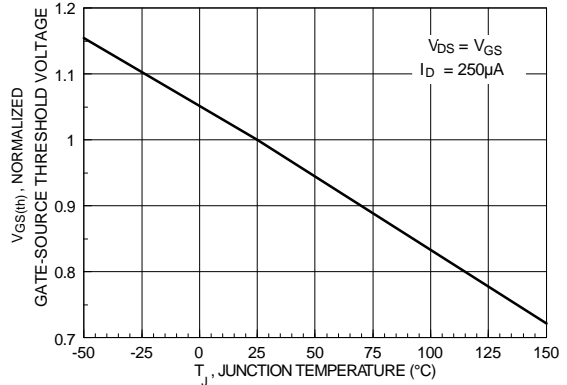


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics

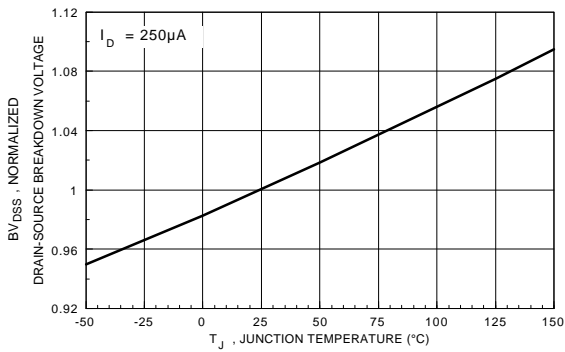


Figure 7. Breakdown Voltage Variation with Temperature.

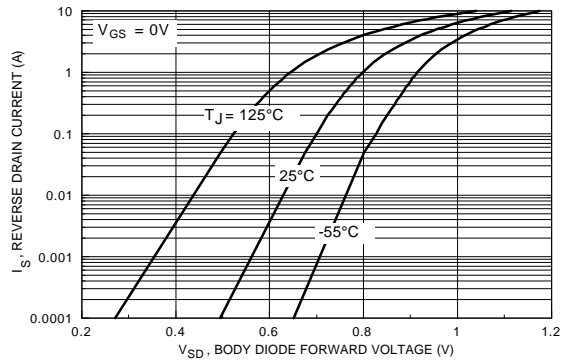


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

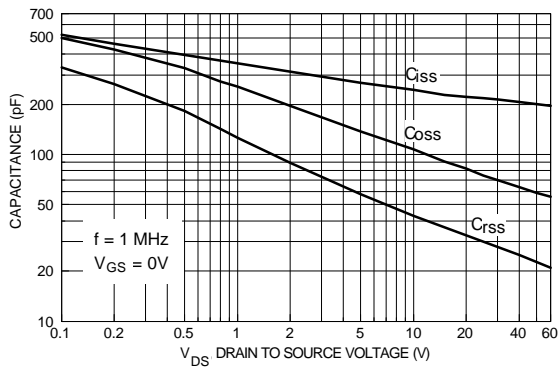


Figure 9. Capacitance Characteristics.

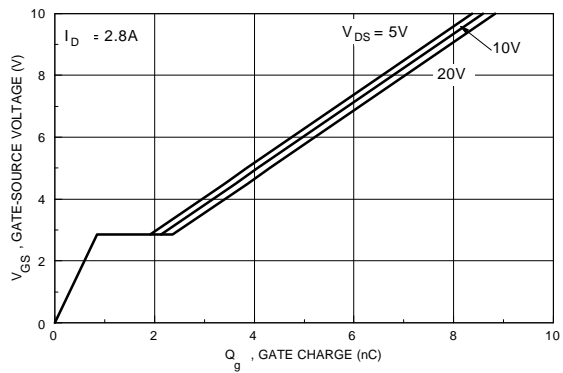


Figure 10. Gate Charge Characteristics.

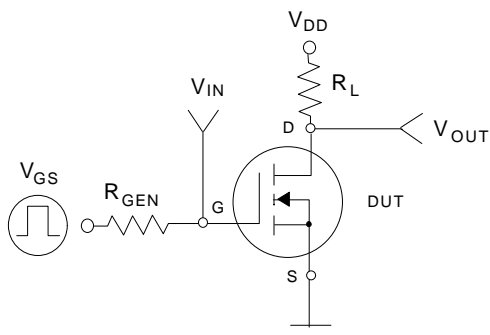


Figure 11. Switching Test Circuit.

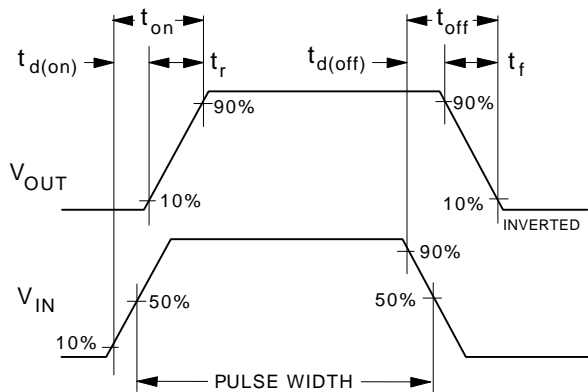


Figure 12. Switching Waveforms.

Typical Thermal Characteristics

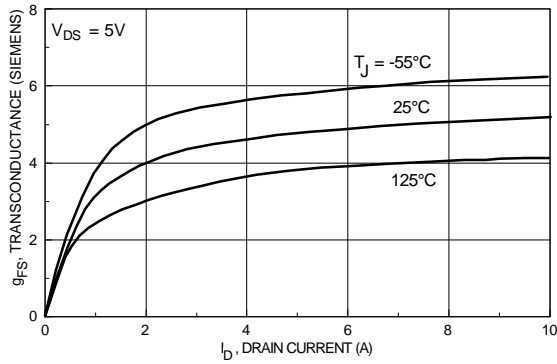


Figure 13. Transconductance Variation with Drain Current and Temperature.

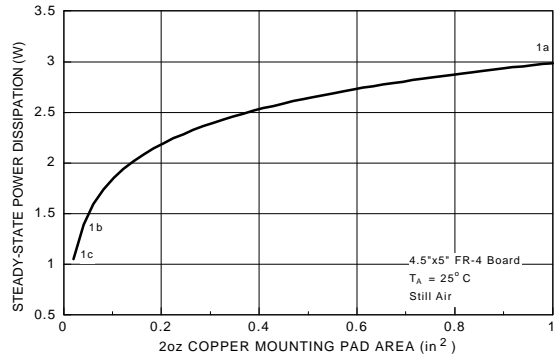


Figure 14. SOT-223 Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

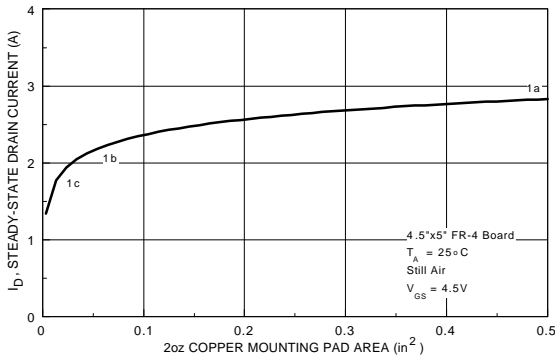


Figure 15. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

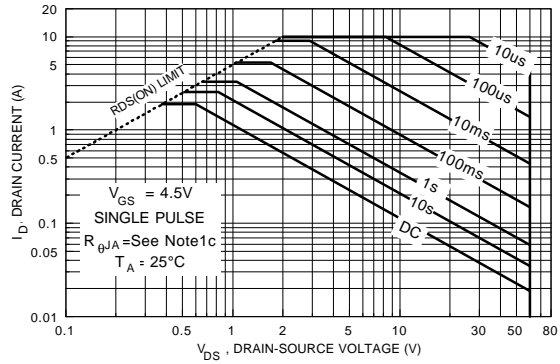


Figure 16. Maximum Safe Operating Area.

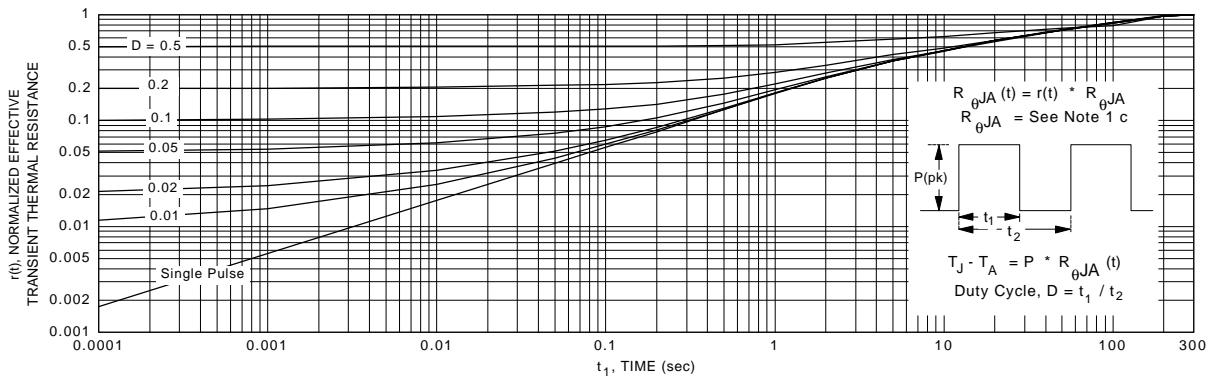


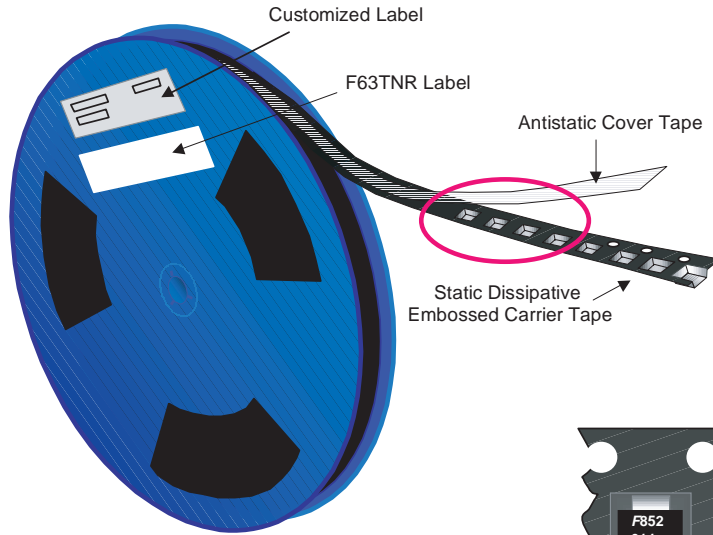
Figure 17. Typical Transient Thermal Impedance Curve.

Remark: Thermal characterization performed under the conditions of Note 1c. Should better thermal design employs, $R_{\theta JA}$ will be lower and reach thermal equivalent sooner.

SOT-223 Tape and Reel Data and Package Dimensions

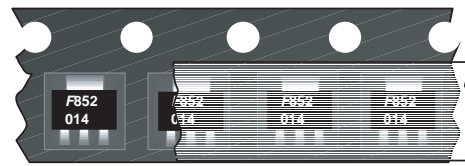


SOT-223 Packaging Configuration: Figure 1.0

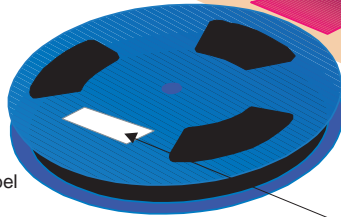
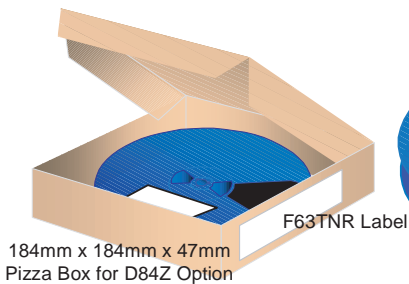
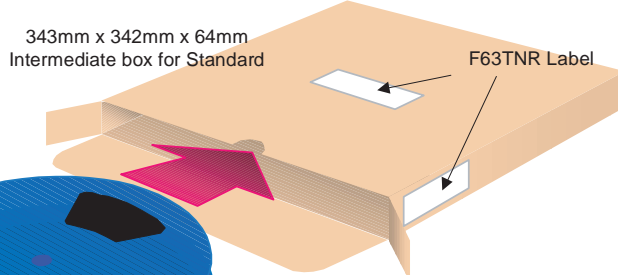


Packaging Description:
 SOT-223 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.
 These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

| SOT-223 Packaging Information | | |
|-------------------------------|-------------------------|------------|
| Packaging Option | Standard (no flow code) | D84Z |
| Packaging type | TNR | TNR |
| Qty per Reel/Tube/Bag | 2,500 | 500 |
| Reel Size | 13" Dia | 7" Dia |
| Box Dimension (mm) | 343x64x343 | 184x187x47 |
| Max qty per Box | 5,000 | 1,000 |
| Weight per unit (gm) | 0.1246 | 0.1246 |
| Weight per Reel (kg) | 0.7250 | 0.1532 |
| Note/Comments | | |



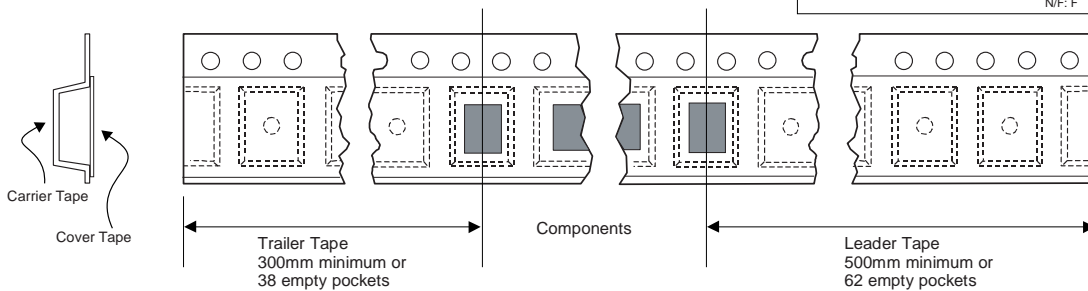
SOT-223 Unit Orientation



F63TNR Label sample

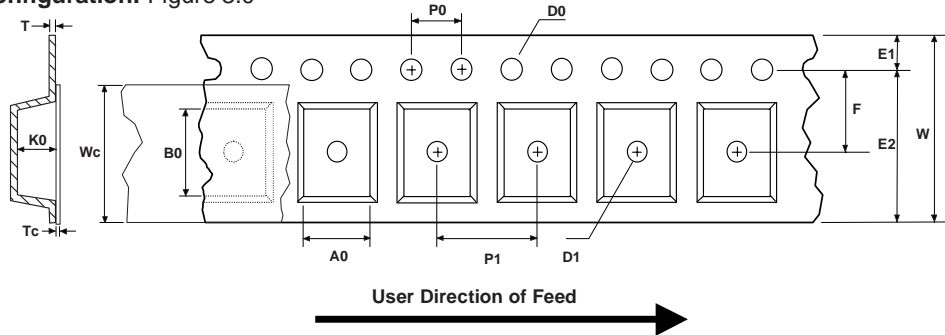
| | |
|------------------|-----------|
| LOT: CBVK741B019 | QTY: 3000 |
| FSID: PN2222A | SPEC: |
| | |
| D/C1: D984Z | QTY1: |
| D/C2: | QTY2: |
| SPEC REV: | CPN: |
| | N/F: F |
| | (F63TNR)3 |

SOT-223 Tape Leader and Trailer Configuration: Figure 2.0



SOT-223 Tape and Reel Data and Package Dimensions, continued

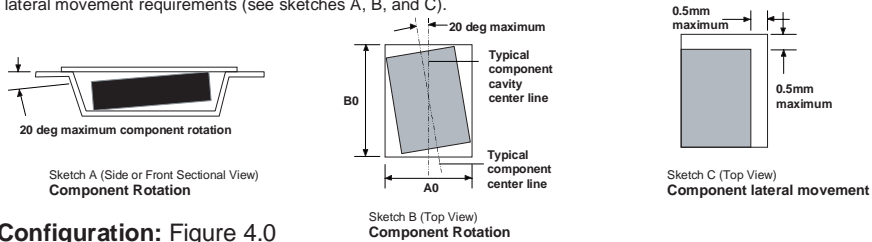
SOT-223 Embossed Carrier Tape Configuration: Figure 3.0



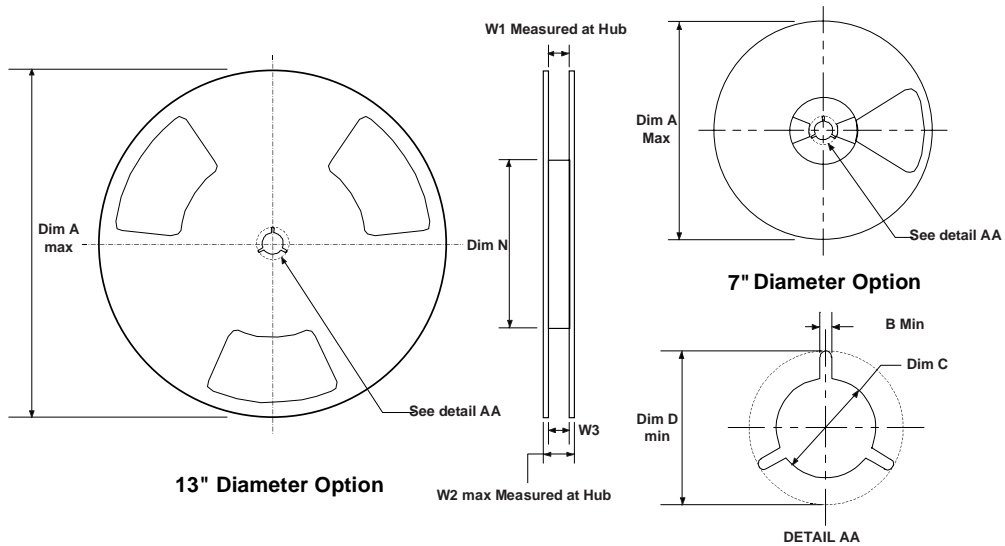
Dimensions are in millimeter

| Pkg type | A0 | B0 | W | D0 | D1 | E1 | E2 | F | P1 | P0 | K0 | T | Wc | Tc |
|----------------|-----------------|-----------------|----------------|-----------------|-----------------|-----------------|--------------|-----------------|---------------|---------------|-----------------|------------------------|-----------------|-----------------|
| SOT-223 (12mm) | 6.83 +/-0.10 | 7.42 +/-0.10 | 12.0 +/-0.3 | 1.55 +/-0.05 | 1.50 +/-0.10 | 1.75 +/-0.10 | 10.25 min | 5.50 +/-0.05 | 8.0 +/-0.1 | 4.0 +/-0.1 | 1.88 +/-0.10 | 0.292 +/- 0.0130 | 9.5 +/-0.025 | 0.06 +/-0.02 |

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

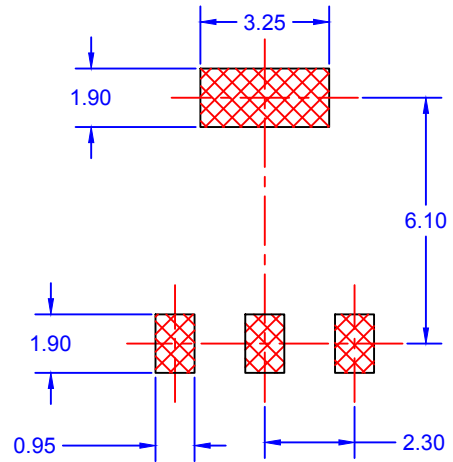


SOT-223 Reel Configuration: Figure 4.0

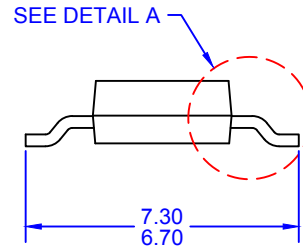
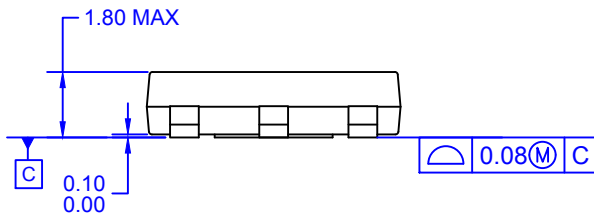


Dimensions are in inches and millimeters

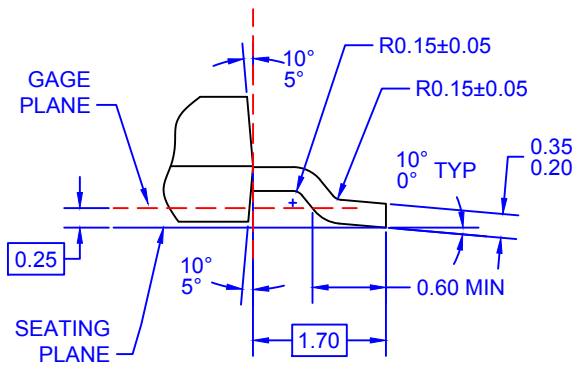
| Tape Size | Reel Option | Dim A | Dim B | Dim C | Dim D | Dim N | Dim W1 | Dim W2 | Dim W3 (LSL-USL) |
|-----------|-------------|---------------|--------------|-----------------------------------|---------------|--------------|----------------------------------|---------------|------------------------------|
| 12mm | 7" Dia | 7.00 177.8 | 0.059 1.5 | 512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 5.906 150 | 0.488 +0.078/-0.000 12.4 +2/0 | 0.724 18.4 | 0.469 - 0.606 11.9 - 15.4 |
| 12mm | 13" Dia | 13.00 330 | 0.059 1.5 | 512 +0.020/-0.008 13 +0.5/-0.2 | 0.795 20.2 | 7.00 178 | 0.488 +0.078/-0.000 12.4 +2/0 | 0.724 18.4 | 0.469 - 0.606 11.9 - 15.4 |



LAND PATTERN RECOMMENDATION



SEE DETAIL A



DETAIL A
SCALE: 2:1

- NOTES: UNLESS OTHERWISE SPECIFIED
 A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.
 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 E) LANDPATTERN NAME: SOT230P700X180-4BN
 F) DRAWING FILENAME: MKT-MA04AREV3



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